### TRADEMARK ASSIGNMENT

### Electronic Version v1.1 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	Security Agreement

#### **CONVEYING PARTY DATA**

Name	Formerly	Execution Date	Entity Type
Siliconix Incorporated		08/08/2013	CORPORATION: DELAWARE

### **RECEIVING PARTY DATA**

Name:	JPMorgan Chase Bank, N.A., as Administrative Agent
Street Address:	10 S. DEARBORN, 7TH FL
City:	Chicago
State/Country:	ILLINOIS
Postal Code:	60603
Entity Type:	N.A.: UNITED STATES

### PROPERTY NUMBERS Total: 4

Property Type	Number	Word Mark
Registration Number:	3929833	MICROBUCK
Registration Number:	4053107	SILICONIX
Registration Number:	4060661	THUNDERFET
Registration Number:	4198891	VRPOWER

### **CORRESPONDENCE DATA**

**Fax Number**: 8668265420

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent

via US Mail.

Phone: 301-638-0511

Email: ipresearchplus@comcast.net

Correspondent Name: IP Research Plus, Inc. Address Line 1: 21 Tadcaster Circle

Address Line 2: attn: Penelope J.A. Agodoa
Address Line 4: Waldorf, MARYLAND 20602

ATTORNEY DOCKET NUMBER: CRS1-38900

TRADEMARK REEL: 005105 FRAME: 0896 D \$115 00 393933

900265458

NAME OF SUBMITTER:	Penelope J.A. Agodoa
Signature:	/pja/
Date:	09/05/2013
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PATENT AND TRADEMARK SECURITY AGREEMENT dated as of August 8, 2013 (this "Agreement"), among Vishay Intertechnology, Inc. (the "Company"), the Domestic Subsidiaries of the Company listed on the signature pages hereto (collectively, together with the Company, the "Grantors") and JPMORGAN CHASE BANK, N.A. ("JPMCB"), as Administrative Agent.

Reference is made to (a) the Credit Agreement dated as of December 1, 2010, as amended and restated as of the date hereof (as further amended, restated, amended and restated, supplemented or otherwise modified from time to time, the "Credit Agreement'), among the Company, the Subsidiary Borrowers from time to time party thereto, the Lenders from time to time party thereto and JPMCB, as Administrative Agent, and (b) Guarantee and Collateral Agreement dated as of December 1, 2010 (as amended, restated, supplemented or otherwise modified from time to time, the "Collateral Agreement"), among the Company, the Domestic Subsidiary Loan Parties from time to time party thereto and JPMCB, as Administrative Agent. The Lenders and Issuing Banks have extended, and have agreed to extend, credit to the Borrowers on the terms and subject to the conditions set forth in the Credit Agreement. The obligations of the Lenders and the Issuing Banks to extend such credit are conditioned upon, among other things, the execution and delivery of this Agreement. The Grantors are Affiliates of the Borrowers, will derive substantial benefits from the extension of credit to the Borrowers under the Credit Agreement and are willing to execute and deliver this Agreement in order to induce the Lenders and Issuing Banks to extend such credit. Accordingly, the parties hereto agree as follows:

SECTION 1. <u>Terms.</u> Each capitalized term used but not otherwise defined herein shall have the meaning specified in the Credit Agreement or the Collateral Agreement, as applicable. The rules of construction specified in Section 1.03 of the Credit Agreement also apply to this Agreement, <u>mutatis mutandis</u>.

SECTION 2. Grant of Security Interest. As security for the payment or performance, as the case may be, in full of the Secured Obligations, each Grantor, pursuant to the Collateral Agreement, did and hereby does grant to the Administrative Agent, its successors and assigns, for the benefit of the Secured Parties, a security interest in all right, title and interest in, to and under any and all of the following assets and properties now owned or at any time hereafter acquired by such Grantor or in which such Grantor now has or at any time hereafter may acquire any right, title or interest (collectively, the "Patent and Trademark Collateral"):

all letters patent of the United States, all registrations and recordings thereof, and all applications for letters patent of the United States, including registrations, recordings and pending applications in the United States Patent and Trademark Office, including those listed on Schedule I;

[[3423590]]

all reissues, continuations, divisions, continuations-in-part, renewals or extensions thereof, and the inventions disclosed or claimed therein, including the right to make, use and/or sell the inventions disclosed or claimed therein;

all trademarks, service marks, trade names, corporate names, company names, business names, fictitious business names, trade styles, trade dress, logos, other source or business identifiers, designs and general intangibles of like nature, now existing or hereafter adopted or acquired, all registrations and recordings thereof, and all registration and recording applications filed in connection therewith, including registrations and registration applications in the United States Patent and Trademark Office or any similar offices in any State of the United States, and all extensions or renewals thereof, including those listed on Schedule II;

all goodwill associated therewith or symbolized thereby; and

all other assets, rights and interests that uniquely reflect or embody such goodwill;

<u>provided</u>, <u>however</u>, that notwithstanding the foregoing, in no event shall the Patent and Trademark Collateral include any Excluded IP Collateral.

SECTION 3. <u>Collateral Agreement</u>. The security interests granted to the Administrative Agent herein are granted in furtherance, and not in limitation of, the security interests granted to the Administrative Agent pursuant to the Collateral Agreement. Each Grantor hereby acknowledges and affirms that the rights and remedies of the Administrative Agent with respect to the Patent and Trademark Collateral are more fully set forth in the Collateral Agreement, the terms and provisions of which are hereby incorporated herein by reference as if fully set forth herein. In the event of any conflict between the terms of this Agreement and the Collateral Agreement, the terms of the Collateral Agreement shall govern.

SECTION 4. <u>Counterparts.</u> This Agreement may be executed in counterparts (and by different parties hereto on different counterparts), each of which shall constitute an original, but all of which when taken together shall constitute a single contract. Delivery of an executed counterpart to a signature page of this Agreement by facsimile or other electronic imaging shall be effective as delivery of a manually executed counterpart of this Agreement.

SECTION 5. <u>Governing Law.</u> This Agreement shall be construed in accordance with and governed by the law of the State of New York.

[Remainder of this page intentionally left blank]

IN WITNESS WHEREOF, the parties hereto have duly executed this Agreement as of the day and year first above written.

VISHAY INTERTECHNOLOGY, INC.,

Ву

Name: David E. McConnell

Title: Vice President and Corporate

Treasurer

VISHAY DALE ELECTRONICS, INC. SILICONIX INCORPORATED VISHAY SPRAGUE, INC.

 $\mathbf{B}\mathbf{y}$ 

Name: David E. McConnell

Title: Treasurer

JPMORGAN CHASE BANK, N.A., as
Administrative Agent,

by
Name: Peter M. Killea
Title: Senior Vice President

Name Phosis Siles Bibe Second Vice Processo

# Schedules to Amended and Restated Patent and Trademark Security Agreement

<u>Patents</u>
See the attached charts.
Patent Applications
See the attached charts.
<u>Trademarks</u>
See the attached charts.
Trademark Applications
See the attached charts.

#20383806 v2

# Patents and Trademarks of Vishay Dale Electronics, Inc.

# (a) <u>U.S. Patent Registrations and Patent Applications</u>

	<u>Type</u>	Serial No. Patent	<u>Title:</u>	<u>Status</u>	File Date	Issue Date	Domestic Loan Party
		<u>No.</u>	(Patent Description)				
1.	UTL	13/689,928	SURFACE MOUNT	PENDING	11/30/2012		Vishay Dale Electronics, Inc.
			RESISTOR WITH				
			TERMINALS FOR HIGH				
			POWER DISSIPATION				
			AND METHOD FOR				
			MAKING SAME				
2.	UTL	13/109,576	METHOD FOR MAKING A	PENDING	5/17/2011		Vishay Dale Electronics, Inc.
			HIGH CURRENT LOW				
			PROFILE INDUCTOR				
3.	UTL	13/127,838	FOUR-TERMINAL	PENDING	5/5/2011		Vishay Dale Electronics, Inc.
			RESISTOR WITH FOUR				
			RESISTORS AND				
			ADJUSTABLE				
			TEMPERATURE				
			COEFFICIENT OF				
4	TITT	12/212 077	RESISTANCE	DEVIDING	0/10/0011		7/1 D 1 P1 . ' T
4.	UTL	13/213,877	HIGH POWERED	PENDING	8/19/2011		Vishay Dale Electronics, Inc.
			INDUCTORS USING A				
5.	TITT	13/462,958	MAGNETIC BIAS	PENDING	5/1/2012		Vichay Dala Elaatuaniaa Ina
٦.	UTL	13/402,938	HEAT SPREADER FOR ELECTRICAL	PENDING	3/1/2012		Vishay Dale Electronics, Inc.
			COMPONENTS				
6.	UTL	13/493,402	RESISTOR WITH	PENDING	6/11/2012		Vishay Dale Electronics, Inc.
0.	VIL	13/493,402	TEMPERATURE	PENDING	0/11/2012		Visitay Date Electronics, inc.
			COEFFICIENT OF				
			RESISTANCE (TCR)				
			COMPENSATION				
7.	UTL	13/569,721	RESISTOR AND METHOD	PENDING	8/8/2012		Vishay Dale Electronics, Inc.
/ '	VIL	13/307,721	FOR MAKING SAME	ILITIDING	0/0/2012		Timay Date Dicettonics, inc.

	Type	Serial No.	<u>Patent</u>	Title:	<u>Status</u>	File Date	Issue Date	Domestic Loan Party
			<u>No.</u>	(Patent Description)				
8.	UTL	13/600,770		HIGHLY COUPLED	PENDING	8/31/2012		Vishay Dale Electronics, Inc.
				INDUCTOR				
9.	UTL	13/720,618		METHOD FOR MAKING	PENDING	12/19/2012		Vishay Dale Electronics, Inc.
				INDUCTOR COIL				
				STRUCTURE				
10.	UTL	13/750,404		INTEGRATED CIRCUIT	PENDING	1/25/2013		Vishay Dale Electronics, Inc.
				ELEMENT AND				
				ELECTRONIC CIRUIT				
				FOR LIGHT EMITTING				
		10/500 500		DIODE APPLICATIONS		4/8.5/8.04.8		
11.	UTL	13/750,762		LOW PROFILE HIGH	PENDING	1/25/2013		Vishay Dale Electronics, Inc.
				CURRENT COMPOSITE				
12	T TODA	12/7/0 020		TRANSFORMER	DENDING	0/45/0040		II'l Di Di I
12.	UTL	13/768,039		INDUCTOR WITH	PENDING	2/15/2013		Vishay Dale Electronics, Inc.
				THERMALLY STABLE				
10	DDA	(1/501.010		RESISTANCE	DENIDING	1/0//0012		Wishes Dela Flactors in Jac
13.	PRV	61/591,018		INTEGRATED CIRCUIT	PENDING	1/26/2012		Vishay Dale Electronics, Inc.
				ELEMENT AND ELECTRONIC CIRCUIT				
				FOR LIGHT EMITTING				
				DIODE APPLICATIONS				
14.	PRV	61/751,562		WIRELESS SIDE	PENDING	1/11/2013		Vishay Dale Electronics, Inc.
17.	110.4	01//31,302		CHARGING	I LINDING	1/11/2013		Visitay Date Dicetonies, inc.
15.	PRV	61/752,278		ELECTRONIC MODULE	PENDING	1/14/2013		Vishay Dale Electronics, Inc.
10.	INY	017732,270		AND METHOD FOR	LIMDING	1/17/2013		Visitay Date Electronics, inc.
				MAKING SAME				
16.	UTL	12/134,240	8,004,379	HIGH POWERED	ISSUED	6/6/2008	8/23/2011	Vishay Dale Electronics, Inc.
10.	V12	12/10/1,2/0	0,001,077	INDUCTORS USING A	100022	0,012000	0/20/2011	+ ising Bail Birthonies, mer
				MAGNETIC BIAS				
17.	UTL	13/096,715	8,258,907	HIGHLY COUPLED	ISSUED	4/28/2011	9/4/2012	Vishay Dale Electronics, Inc.
		,,,,	, ,,,,,,,	INDUCTOR	·			, , , , , , , , , , , , , , , , , , , ,
18.	UTL	12,950,177	8,319,598	POWER RESISTOR	ISSUED	11/19/2010	11/27/2012	Vishay Dale Electronics, Inc.
19.	UTL	13/051,585	8,344,843	RESISTOR AND METHOD	ISSUED	3/18/2011	1/1/2013	Vishay Dale Electronics, Inc.
				FOR MAKING SAME				

		Serial No.	Patent No.	Title: (Patent Description)	<u>Status</u>	File Date	Issue Date	<u>Domestic Loan Party</u>
20.	UTL	13/198,274	8,378,772	INDUCTOR WITH	ISSUED	8/4/2011	2/19/2013	Vishay Dale Electronics, Inc.
				THERMALLY STABLE				
				RESISTANCE				

The Company previously decided to abandon the following patents:

	Type	Serial No.	Patent No.	Title: (Patent Description)	<u>Status</u>	<u>File Date</u>	<u>Issue Date</u>	Domestic Loan Party
1.	UTL	13/213,877		HIGH POWERED INDUCTORS USING A	CLOSED	8/19/2011		Vishay Dale Electronics, Inc.
				MAGNETIC BIAS				
2.	UTL	13/589,533		METAL STRIP RESISTOR	CLOSED	8/16/2012		Vishay Dale Electronics, Inc.
				FOR MITIGATING EFFECTS				
				OF THERMAL EMF				
3.	UTL	13/684,781		POWER RESISTOR	CLOSED	11/26/2012		Vishay Dale Electronics, Inc.
4.	UTL	08/936,193	5,922,514	THICK FILM LOW VALUE	CLOSED	9/17/1997	7/13/1999	Dale Electronics, Inc. <sup>1</sup>
				HIGH FREQUENCY				
				INDUCTOR, AND METHOD				
				OF MAKING THE SAME				
5.	UTL	08/881,480	5,970,604	METHOD OF MAKING A	CLOSED	6/24/1997	10/26/1999	Dale Electronics, Inc. <sup>2</sup>
				MONOLITHIC THICK FILM				
				INDUCTOR				
6.	UTL	09/774,854	6,587,025	SIDE-BY-SIDE COIL	CLOSED	1/31/2001	7/1/2003	Vishay Dale Electronics, Inc.
				INDUCTOR				

## **License Agreements (Patents)**

 $<sup>^{1}</sup>$  Filed with USPTO as Dale Electronics, Inc., but the name was changed to Vishay Dale Electronics, Inc. on June 4, 1997.

<sup>&</sup>lt;sup>2</sup> Filed with USPTO as Dale Electronics, Inc., but the name was changed to Vishay Dale Electronics, Inc. on June 4, 1997.

	Name of Licensor	Name of Agreement	Date of Agreement	Parties to Agreement:
7.	Vishay Dale	Non-Exclusive License Agreement	Effective date of	Vishay Dale Electronics, Inc. (as
	Electronics, Inc.		December 31, 2012	licensor) and TRIO Technology
				Co., Ltd. (as licensee)
8.	Vishay Dale	Amended and Restated Non-Exclusive License	January 10, 2013	Vishay Dale Electronics, Inc. (as
	Electronics, Inc.	Agreement		licensor) and AOBA Technology
				(M) Sdn. Bhd. (as licensee) and
				ABC Taiwan Electronics Corp. (as
				co-licensee)
9.	Vishay Dale	Vishay Non-Exclusive License Agreement	Effective date of	Vishay Dale Electronics, Inc. (as
	Electronics, Inc.		January 14, 2013	licensor) and Chilisin Electronics
			·	Corporation (as licensee)
10.	Vishay Dale	Non-Exclusive License Agreement	Effective date as of	Vishay Dale Electronics, Inc. (as
	Electronics, Inc.	_	February 28, 2013	licensor) and Hotline (Shenzhen)
				Electronic Co., LTD (as licensee)

# (b) <u>U.S. Trademarks and Trademark Applications</u>

The Company previously decided to abandon the following trademarks:

<u>I rademark</u>					Renewal due
THERMALLOY	Vishay Dale	United	N/A	N/A	N/A
	Electronics, Inc.	States			

## **License Agreements (Trademarks)**

None.

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## Patents and Trademarks of Vishay Intertechnology, Inc.

#### **U.S. Patent Registrations and Patent Applications** (a)

	Type	Serial No.	Patent No.	<u>Title:</u>	<u>Status</u>	File Date	Issue Date	Domestic Loan Party
				(Patent Description)				
1.	UTL	13/592,091		PRECISION HIGH-	PENDING	12/3/2012		Vishay Intertechnology, Inc.
				FREQUENCY CAPACITOR				
				FORMED ON				
				SEMICONDUCTOR				
				SUBSTRATE				
2.	UTL	11/759,523	7,907,090	CERAMIC DIELECTRIC	ISSUED	6/7/2007	3/15/2011	Vishay Intertechnology, Inc.
				FORMULATION FOR BROAD				
				BAND UHF ANTENNA				
3.	UTL	13/075,752	8,324,711	PRECISION HIGH	ISSUED	3/30/2011	12/4/2012	Vishay Intertechnology, Inc.
				FREQUENCY CAPACITOR				
				FORMED ON				
				SEMICONDUCTOR				
				SUBSTRATE				

The Company previously decided to abandon the following patents:

	Type	Serial No.	Patent No.	Title: (Patent Description)	<u>Status</u>	File Date	Issue Date	<u>Domestic Loan Party</u>
1.	UTL	13/567,317		BULK CAPACITOR AND METHOD	PENDING	8/6/2012		Vishay Intertechnology, Inc.

### **License Agreements (Patents):**

None

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#### U.S. Trademarks and Trademark Applications **(b)**

None

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The Company previously decided to abandon the following trademarks:

<u>Trademark</u>	Legal Owner	Country	Reg.#	Reg. Date	Renewal due
FUNCTIONPAK	Vishay Intertechnology,	United States	2602606	7/30/2002	7/30/2022
	Inc.				
VISHAY (Triangle & Circle	Vishay Intertechnology,	United States	1687032	5/12/1992	5/12/2012
Design)	Inc.				
VISHAY	Vishay Intertechnology,	United States	1689517	5/26/1992	5/26//2012
INTERTECHNOLOGY	Inc.				

## **License Agreements (Trademarks)**

None.

# Patents and Trademarks of Siliconix incorporated

# (a) <u>U.S. Patent Registrations and Patent Applications</u>

	<u>Type</u>	Serial No.	Patent No.	Title:	<u>Status</u>	File Date	Issue Date	<b>Domestic Loan Party</b>
				(Patent Description)				
1.	UTL			TRANSISTOR	PENDING			Siliconix incorporated
				STRUCTURE WITH				
				FEED-THROUGH				
				SOURCE-TO -				
				SUBSTRATE				
				CONTACT				
2.	UTL			STRUCTURES OF AND	PENDING			Siliconix incorporated
				METHODS OF				
				FABRICATING DUAL				
				GATE MIS DEVICES				
3.	UTL			SEE VISH-11671-1D	PENDING			Siliconix incorporated
4.	UTL	11/373,630		NARROW	PENDING	3/9/2006		Siliconix incorporated
				SEMICONDUCTOR				
				TRENCH STRUCTURE				
5.	UTL	11/479,619		POWER	PENDING	6/30/2006		Siliconix incorporated
				MANAGEMENT				
				SYSTEM				
				IMPEMENTED IN A				
				SINGLE SURFACE				
				MOUNT PACKAGE				
6.	UTL	11/582,755		CHIP SCALE	ALLOWED	5/11/2011		Siliconix incorporated
				SCHOTTKY DEVICE				
7.	UTL	11/644,553		HIGH MOBILITY	PENDING	12/22/2006		Siliconix incorporated
				POWER METAL-				
				OXIDE				
				SEMICONDUCTOR				
				FIELD-EFFECT				
				TRANSISTORS				

	<u>Type</u>	Serial No.	Patent No.	Title:	<u>Status</u>	File Date	Issue Date	Domestic Loan Party
				(Patent Description)				
8.	UTL	11/651,258		HIGH-DENSITY	PENDING	1/8/2007		Siliconix incorporated
				POWER MOSFET				
				WITH PLANARIZED				
				METALIZATION				
9.	UTL	13/039,098		STRUCTURES OF AND	PENDING	3/2/2011		Siliconix incorporated
				METHODS OF				
				FABRICATING DUAL				
				GATE DEVICES				
10.	UTL	13/229,667		DUAL LEAD FRAME	PENDING	9/9/2011		Siliconix incorporated
				SEMICONDUCTOR				
				PACKAGE AND				
				METHOD OF				
				MANUFACTURE				
11.	UTL	13/308,375		TRENCH	PENDING	11/30/2011		Siliconix incorporated
				POLYSILICON DIODE				
12.	UTL	13/370,243		STRUCTURES OF AND	FILED	2/9/2012		Siliconix incorporated
				METHODS OF				
				FABRICATING				
				POWERMOS WITH				
				TERMINATION				
				TRENCH HAVING				
				THICK OXIDE FOR				
12	TITEL	12///0.5/7		THE HIGH BDdss	DENIDING	4/20/2012		0.11
13.	UTL	13/460,567		HYBRID SPLIT GATE	PENDING	4/30/2012		Siliconix incorporated
1.4	T JODA	12///0 /00		SEMICONDUCTOR METHOD OF	DEMINIC	4/20/2012		0'11'' ' ' ' ' ' ' '-
14.	UTL	13/460,600		METHOD OF	PENDING	4/30/2012		Siliconix incorporated
				FORMING A HYBRID				
				SPLIT GATE				
				SEMICONDUCTOR				

	<u>Type</u>	Serial No.	Patent No.	Title:	<u>Status</u>	File Date	Issue Date	Domestic Loan Party
15.	UTL	13/475,255		(Patent Description)  SEMICONDUCTOR DEVICE HAVING REDUCED GATE CHARGES AND SUPERIOR FIGURE OF MERIT	PENDING	5/18/2012		Siliconix incorporated
16.	UTL	13/478,037		STACKED TRENCH METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR DEVICE	PENDING	5/22/2012		Siliconix incorporated
17.	UTL	13/484,114		ADAPTIVE CHARGE BALANCED EDGE TERMINATION	PENDING	5/30/2012		Siliconix incorporated
18.	UTL	13/551,516		CURRENT MODE BOOST CONVERTER USING SLOPE COMPENSATION	PENDING	7/17/2012		Siliconix incorporated
19.	UTL	13/565,672		PREVENTING REVERSE CONDUCTION	PENDING	8/2/2012		Siliconix incorporated
20.	UTL	13/622,322		HIGH CURRENT DENSITY POWER FIELD EFFECT TRANSISTOR	PENDING	9/18/2012		Siliconix incorporated
21.	UTL	13/622,997		BREAKDOWN VOLTAGE BLOCKING DEVICE	PENDING	9/19/2012		Siliconix incorporated
22.	UTL	13/654,230		POWER MOSFET CONTACT METALIZATION	PENDING	10/17/2012		Siliconix incorporated

	<u>Type</u>	Serial No.	Patent No.	Title:	<u>Status</u>	File Date	Issue Date	Domestic Loan Party
				(Patent Description)				
23.	UTL	13/728,997		TRENCH METAL	PENDING	12/27/2012		Siliconix incorporated
				OXIDE				
				SEMICONDUCTOR				
				WITH RECESSED				
				TRENCH MATERIAL				
				AND REMOTE				
				CONTACTS				
24.	UTL	13/732,284		ADAPTIVE CHARGE	PENDING	12/31/2012		Siliconix incoporated
				BALANCED MOSFET				
				TECHNIQUES				
25.	UTL	13/829,623		POWER MOSFET	PENDING	3/14/2013		Siliconix incorporated
				PACKAGE WITH				
				STACK DIE, LDMOS				
				DIE STRUCTURE, FLIP				
				CHIP ON LEADFRAME				
				AND SOURCE, DRAIN				
				AND GATE CLIPS				
26.	UTL	13/830,041		METHOD OF	PENDING	3/14/2013		Siliconix incorporated
				FABRICATING				
				STACKED DIE				
				PACKAGE				
27.	UTL	13/867,964		CURRENT LIMITING	PENDING	4/22/2013		Siliconix incorporated
				SYSTEMS AND				
				METHODS				2
28.	ŲTL	08/487,789	5,925,411	GAS-BASED	ISSUED	6/7/1995	7/20/1999	[Siliconix incorporated] <sup>3</sup>
				SUBSTRATE				
				DEPOSITION				
				PROTECTION				

<sup>&</sup>lt;sup>3</sup> To be confirmed.

# <u>License Agreements (Patents)</u>:

	Name of Licensor	Name of Agreement		Parties to Agreement:
1.	Siliconix incorporated	Patent Cross License Agreement	Effective date of	Infineon Technology AG and
			January 1, 2013	Siliconix incorporated

## (b) <u>U.S. Trademarks and Trademark Applications</u>

No.	<u>Trademark</u>	Legal Owner	<u>Country</u>	Reg.#	Reg. Date
1.	MICROBUCK	Siliconix incorporated	United States	3.929,833	12/2/1975
2.	SILICONIX	Siliconix incorporated	United States	4,053,107	11/8/2011
3.	THUNDERFET	Siliconix incorporated	United States	4,060,661	11/22/2011
4.	VRPower	Siliconix incorporated	United States	4,198,891	8/28/2012

## **License Agreements (Trademarks)**

None

### Vishay Sprague, Inc.

**U.S. Patent Registrations and Patent Applications** (a)

None.

## **License Agreements (Patents):**

None.

**U.S. Trademarks and Trademark Applications (b)** 

None.

The Company previously decided to abandon the following trademarks:

<u>Trademark</u>	Legal Owner	Country Country	Reg.#	Reg. Date	<u>Renewal due</u>
MULTIDIAL	Vishay Sprague, Inc.	United States	715,744	5/23/1961	11/23/2011

### **License Agreements (Trademarks):**

None.

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**RECORDED: 09/05/2013**